12. ~~22.~~ (New) The method for manufacturing a semiconductor integrated circuit device according to claim ~~17~~ 7, wherein said flash memory is an NOR type flash memory.

13. ~~23.~~ (New) The method for manufacturing a semiconductor integrated circuit device according to claim ~~11~~ 1, wherein each of said at least one pair of laminating structure bodies constitutes a memory cell of a flash memory, and writing into said memory cell is carried out by injecting a charge into said floating gate electrode.

14. ~~24.~~ (New) The method for manufacturing a semiconductor integrated circuit device according to claim ~~23~~ 13, wherein said flash memory is an NOR type flash memory.

REMARKS

In response to the outstanding restriction requirement, Applicants hereby elect the invention II (Claims 11-21) for examination. Claims 22-24 newly presented herein are directed to the elected invention and